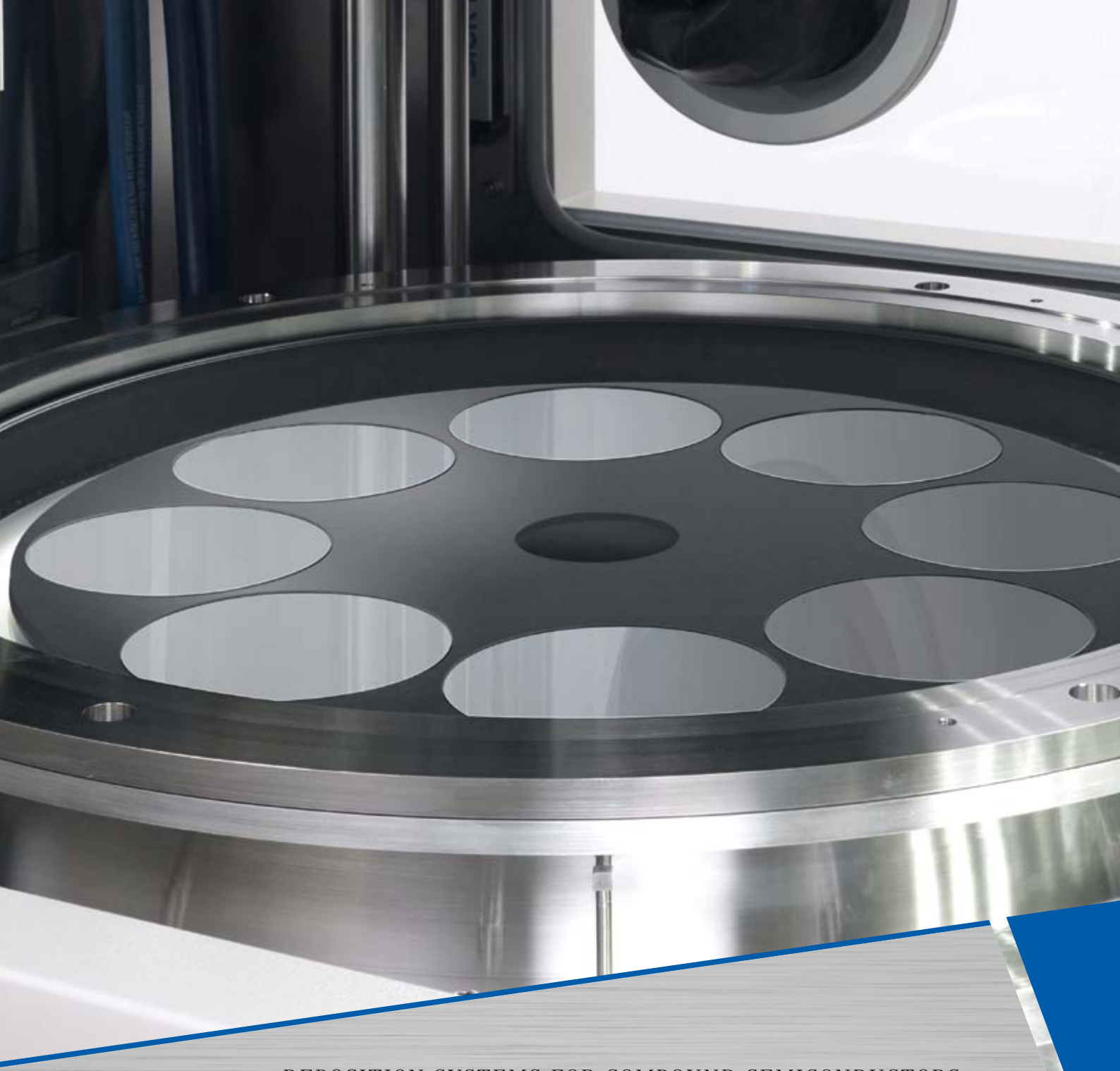


DEPOSITION SYSTEMS FOR COMPOUND SEMICONDUCTORS

AIX G5 WW Planetary Reactor® for 100 mm and 150 mm SiC

AIXTRON

Our technology. Your future.

NEW: 8 x 150 mm & 12 x 100 mm configuration for largest throughput

AIX G5 WW (Warm-Wall) SiC VPE System

Your Benefit

- Largest batch capacity
- Highest throughput
- Lowest cost/wafer
- Optimized epitaxial layer quality

Design Highlights

- Triple flow gas injector - providing process robustness and effective process tuning
- Sandwich susceptor
- Simplified and shortened maintenance cycles

Features

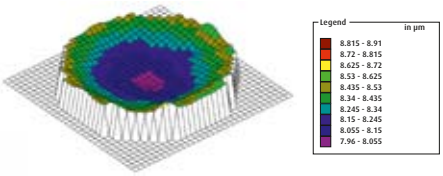
- Flexible reactor capacity: 12 x 100 mm / 8 x 150 mm
- Highest wafer throughput and fast cycle times
- Maximum production yield by improved uniformity
- Enhanced productivity

Optional

- Measuring tool for analysis of wafer surface temperature

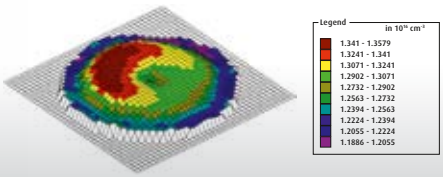
SiC production technology for next generation power electronics

150mm SiC epitaxy results:



Typical thickness uniformity

2.4 % standard deviation with 5 mm EE @ 8.9 µm mean thickness



Typical doping uniformity

3.7 % standard deviation with 5mm EE @ 1.19E16 cm^{-3} mean net donor concentration

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